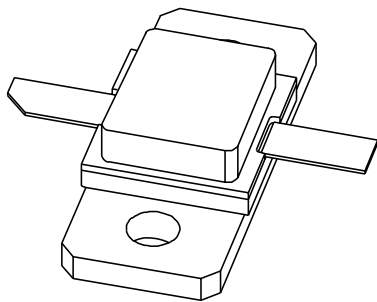


DATA SHEET



PZ1418B30U

NPN microwave power transistor

Product specification
Supersedes data of 1997 Feb 19

1997 Nov 13

NPN microwave power transistor

PZ1418B30U

FEATURES

- Interdigitated structure provides high emitter efficiency
- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Gold metallization realizes very stable characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Internal input and output prematching ensures good stability and easy broadband use.

APPLICATIONS

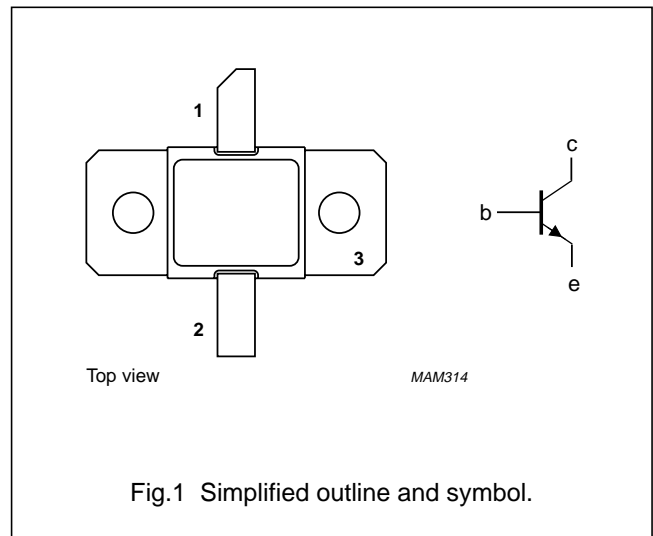
- Common base class-B broadband amplifiers under CW conditions in military and professional applications.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT443A metal ceramic flange package with the base connected to the flange.

PINNING - SOT443A

PIN	DESCRIPTION
1	collector
2	emitter
3	base; connected to flange



QUICK REFERENCE DATA

RF performance up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ in a common base class-B wideband amplifier.

f (GHz)	V _{CC} (V)	P _L (W)	G _p (dB)	η _c (%)	Z _i ; Z _L (Ω)
1.4 to 1.8	28	≥27	≥7.3	≥38	see Figs 6 and 7

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

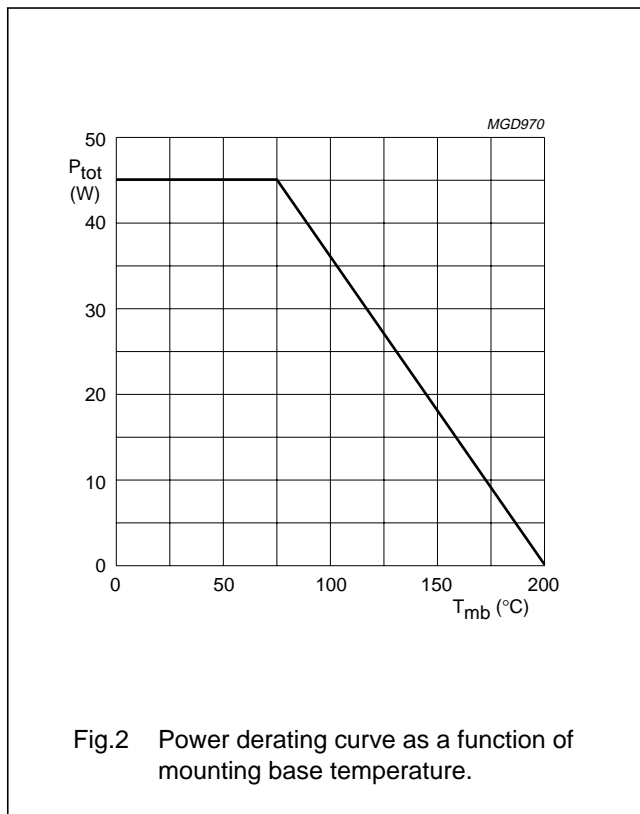
NPN microwave power transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	40	V
V _{CEO}	collector-emitter voltage	open base	–	15	V
V _{CES}	collector-emitter voltage	R _{BE} = 0	–	35	V
V _{EBO}	emitter-base voltage	open collector	–	3	V
I _C	collector current (DC)		–	4	A
P _{tot}	total power dissipation	T _{mb} ≤ 75 °C	–	45	W
T _{stg}	storage temperature		–65	+200	°C
T _j	operating junction temperature		–	200	°C
T _{slid}	soldering temperature		–	235	°C



NPN microwave power transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting-base	$T_j = 75\text{ }^\circ\text{C}$	2.2	K/W
$R_{th\ mb-h}$	thermal resistance from mounting-base to heatsink	$T_j = 75\text{ }^\circ\text{C}$; note 1	0.2	K/W

Note

1. See "Mounting recommendations in the General part of handbook SC19a".

CHARACTERISTICS

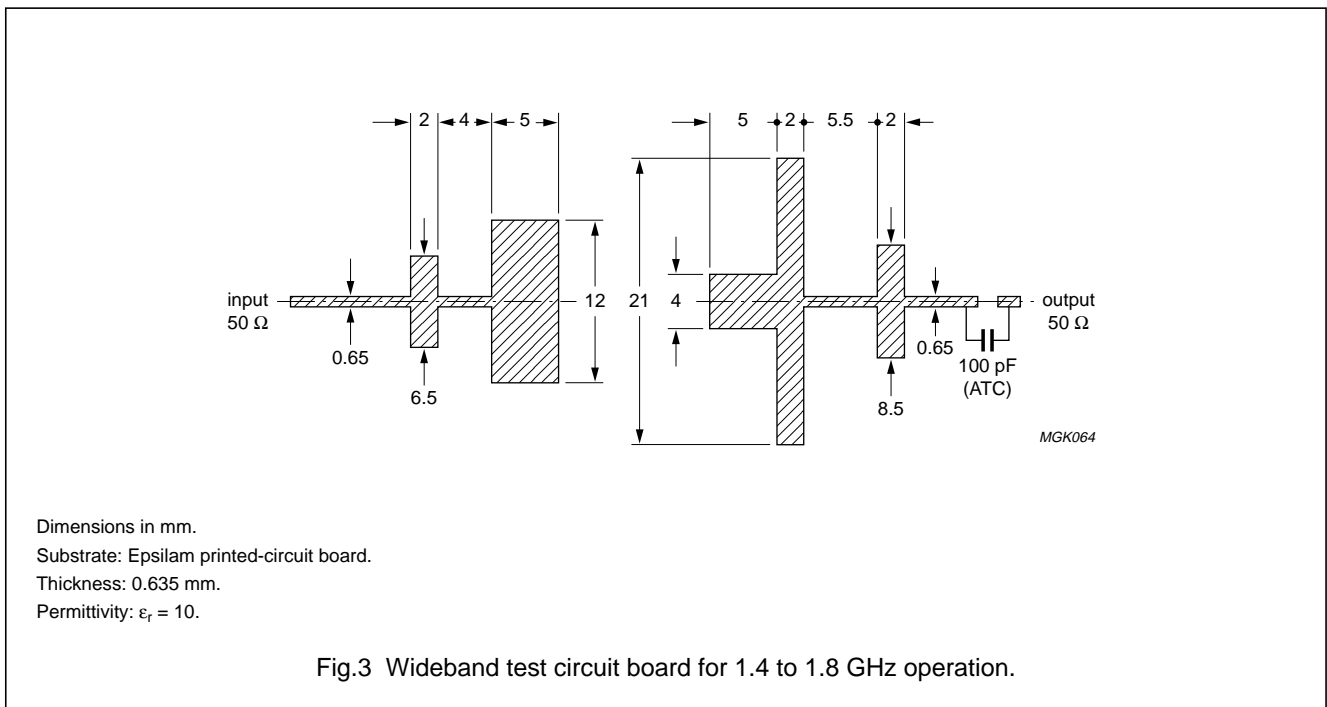
$T_{mb} = 25\text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
I_{cBO}	collector cut-off current	$V_{CB} = 40\text{ V}; I_E = 0$	10	mA
		$V_{CB} = 30\text{ V}; I_E = 0$	5	mA
I_{CES}	collector cut-off current	$V_{CE} = 35\text{ V}; R_{BE} = 0$	50	mA
I_{EBO}	emitter cut-off current	$V_{EB} = 1.5\text{ V}; I_C = 0$	200	μA

APPLICATION INFORMATION

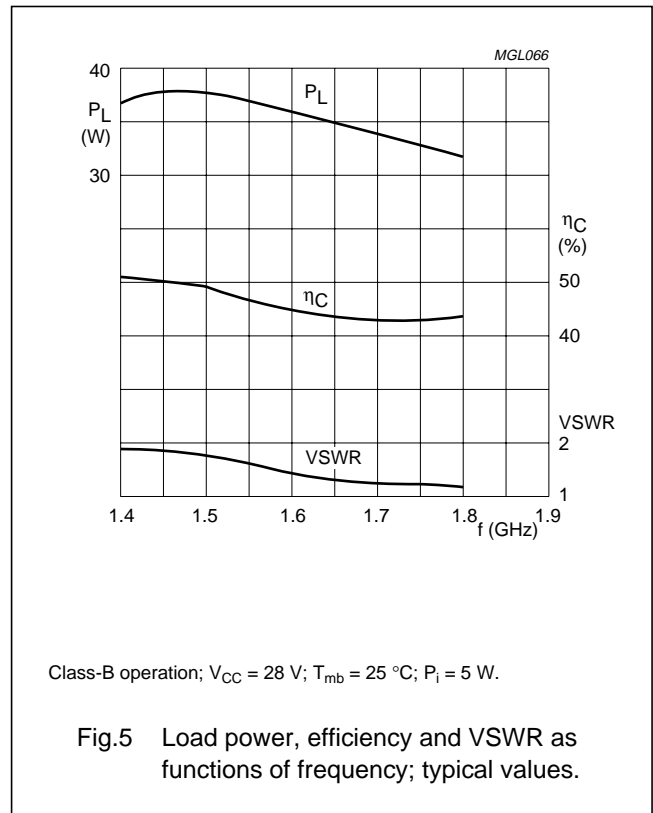
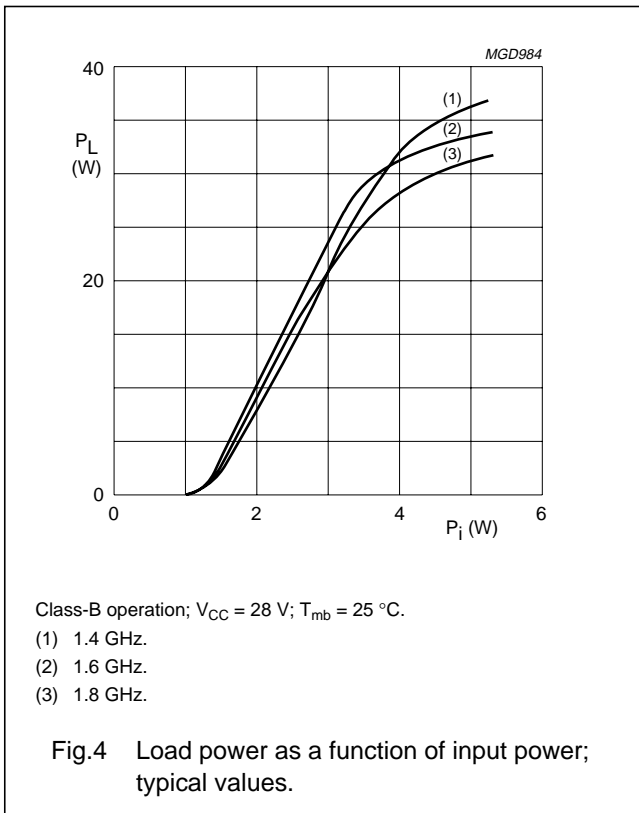
Microwave performance up to $T_{mb} = 25\text{ }^\circ\text{C}$ in a common base class B wideband amplifier.

f (GHz)	V_{CC} (V)	P_L (W)	G_p (dB)	η_c (%)	$Z_i; Z_L$ (Ω)
1.4 to 1.8	28	≥ 27 typ. 35	≥ 7.3 typ. 8.4	≥ 38 typ. 45	see Figs 6 and 7



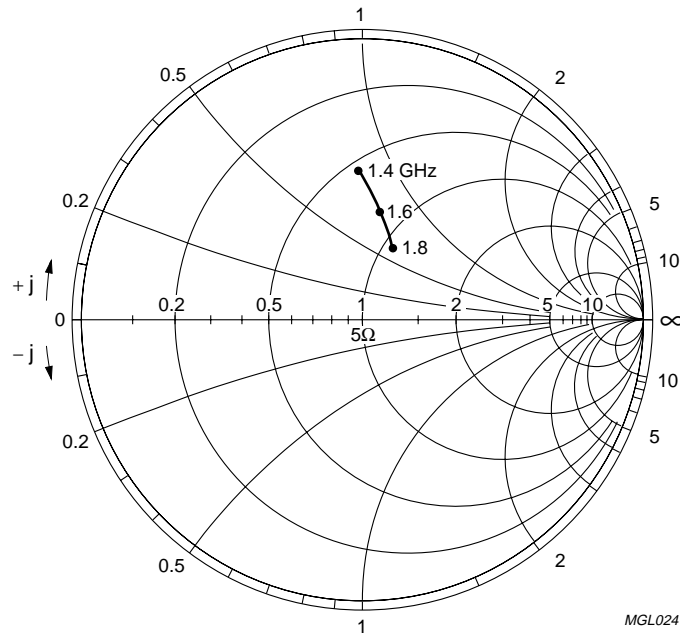
NPN microwave power transistor

PZ1418B30U



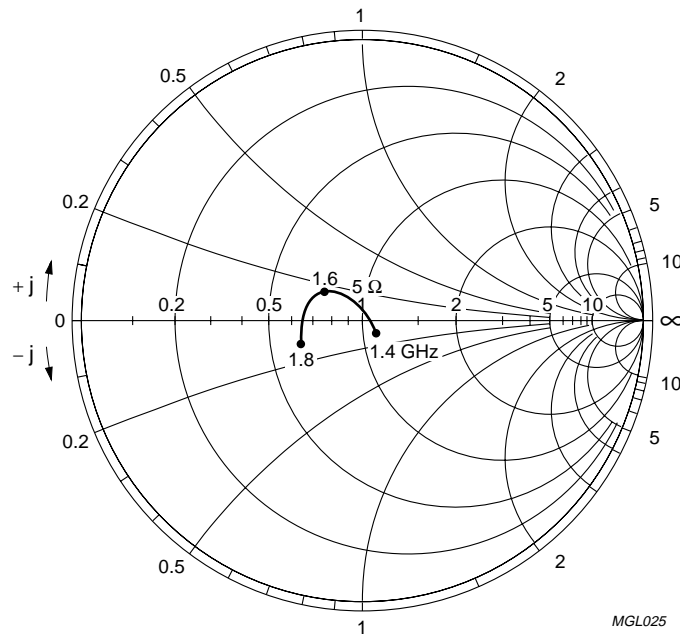
NPN microwave power transistor

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$Z_0 = 5 \Omega$.

Fig.6 Input impedance as a function of frequency; typical values.



$Z_0 = 5 \Omega$.

Fig.7 Optimum load impedance as a function of frequency; typical values.

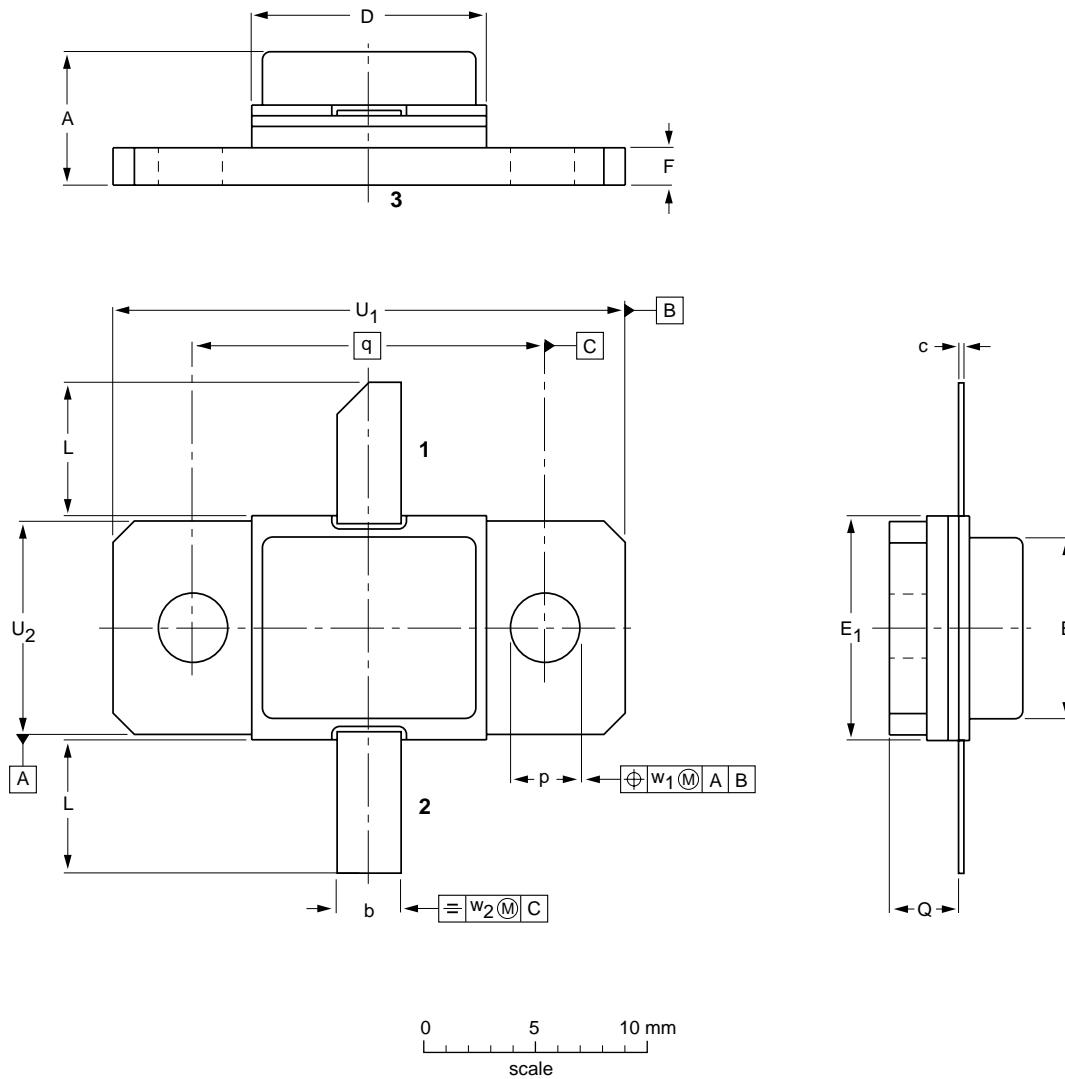
NPN microwave power transistor

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PACKAGE OUTLINE

Flanged hermetic ceramic package; 2 mounting holes; 2 leads

SOT443A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	E	E ₁	F	L	p	Q	q	U ₁	U ₂	w ₁	w ₂
mm	6.33 4.87	3.21 2.89	0.16 0.07	10.47 9.90	8.13 7.87	10.22 9.90	1.61 1.44	6.25 5.74	3.41 3.20	3.61 2.84	16.51	23.12 22.70	9.91 9.70	0.51	1.02

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT443A						97-05-23

NPN microwave power transistor

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NPN microwave power transistor

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NOTES

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NOTES

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NOTES

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